SONY CXK58257ATM/AYM -70LLX/85LLX/10LLX/12LLX

32768-word × 8-bit High Speed CMOS Static RAM

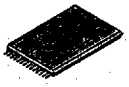
SONY CORP/COMPONENT PRODS

Description

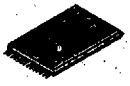
CXK58257ATM/AYM is a 256K bits, 32,768 words by 8 bits, CMOS static RAM.

It is suitable for portable and battery back-up systems which require extremely small package and low stand-by current.

CXK58257ATM
28 pin TSOP (Plastic)



CXK58257AYM
28 pin TSOP (Plastic)



Features

- Extended operation temperature range: –25 to +85°C
- Thin small-outline package:
  CXK58257ATM: 8mm × 13.4mm 28 pin TSOP
  CXK58257AYM: 8mm × 13.4mm 28 pin TSOP
  (Mirror image pinout)
- Low stand-by current:
  10 µA (Max.) @Vcc=5.5V, Ta=–25 to +85°C
- Low voltage data retention: 2.0V (Min.)
- Fast access time: (Access time)
  CXK58257ATM/AYM-70LLX 70ns (Max.)
  CXK58257ATM/AYM-85LLX 85ns (Max.)
  CXK58257ATM/AYM-10LLX 100ns (Max.)
  CXK58257ATM/AYM-12LLX 120ns (Max.)
- Single +5V Supply: 5V ± 10%

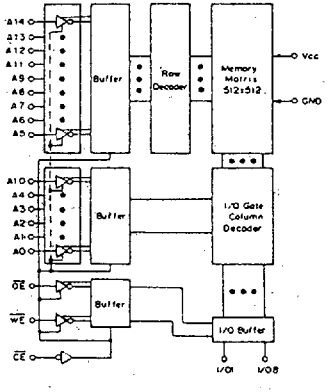
Function

32768-word × 8-bit static RAM

Structure

Silicon gate CMOS IC

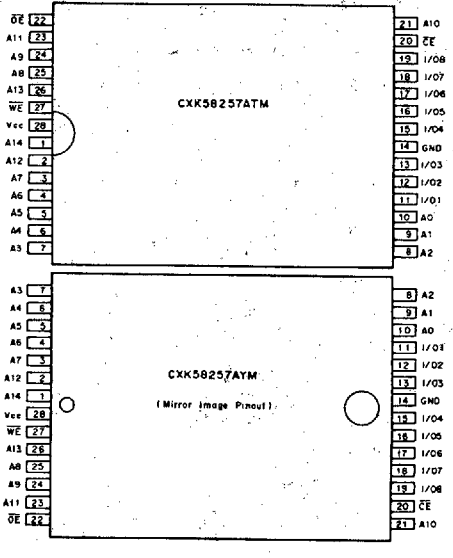
Block Diagram



Pin Description

Symbol	Description
A0 to A14	Address input
I/O1 to I/O8	Data input/output
$\overline{CE}$	Chip enable input
$\overline{WE}$	Write enable input
$\overline{OE}$	Output enable input
Vcc	+5V power supply
GND	Ground

Pin Configuration (Top View)



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Absolute Maximum Ratings (Ta=25℃, GND=0V)

Item	Symbol	Rating	Unit
Supply voltage	V_{CC}	−0.5 to +7.0	V
Input voltage	V_{IN}	−0.5 * to Vcc+0.5	V
Input and output voltage	$V_{I/O}$	−0.5 * to Vcc +0.5	V
Allowable power dissipation	P_D	0.7	W
Operating temperature	Topr	−25 to +85	℃
Storage temperature	Tstg	−55 to +150	℃
Soldering temperature • time	Tsolder	235 • 10	℃ • sec

* V_{IN}, $V_{I/O}$=−3.0V Min. for pulse width less than 50ns.

Truth Table

$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	Mode	I/O1 to I/O8	Vcc Current
H	×	×	Not selected	High Z	I_{SB1}, I_{SB2}
L	H	H	Not selected	High Z	I_{CC1}, I_{CC2}
L	L	H	Read	Data out	I_{CC1}, I_{CC2}
L	×	L	Write	Data in	I_{CC1}, I_{CC2}

× : "H" or "L"

DC Recommended Operating Conditions (Ta=−25 to +85℃, GND=0V)

Item	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	Vcc	4.5	5.0	5.5	V
Input high voltage	V_{IH}	2.2	——	Vcc+0.3	V
Input low voltage	V_{IL}	−0.3 *	——	0.8	V

* V_{IL}=−3.0V Min. for pulse width less than 50ns.

Electrical Characteristics

• DC and operating characteristics (Vcc=5V ± 10%, GND=0V, Ta=–25 to +85°C)

Item	Symbol	Test conditions		–70LLX/85LLX/10LLX/12LLX Min.	Typ.*	Max.	Unit
Input leakage current	I_{LI}	V_{IN}=GND to Vcc		–0.5	—	0.5	µA
Output leakage current	I_{LO}	$\overline{CE}$=V_{IH} or $\overline{OE}$=V_{IH} $V_{I/O}$=GND to Vcc		–0.5	—	0.5	µA
Operating power supply current	I_{CC1}	$\overline{CE}$=V_{IL}, V_{IN}=V_{IH} or V_{IL}, I_{OUT}=0mA		—	3	10	mA
		$\overline{CE}$ ≦ 0.2V V_{IN} ≦ 0.2V or ≧ Vcc–0.2V		—	1	5	
Average operating current	I_{CC2}	Cycle=Min, Duty=100% I_{OUT}=0mA	70LLX	—	30	60	mA
			85LLX	—	25	60	
			10LLX	—	23	60	
			12LLX	—	20	60	
Standby current	I_{SB1}	$\overline{CE}$ ≧ Vcc–0.2V	–25 to +85°C	—	—	10	µA
			–25 to +70°C	—	—	5	
			–25 to +40°C	—	—	1	
			+25°C	—	0.2	0.5	
	I_{SB2}	$\overline{CE}$=V_{IH}		—	0.4	2	mA
Output high voltage	V_{OH}	I_{OH}=–1.0mA		2.4	—	—	V
Output low voltage	V_{OL}	I_{OL}=2.1mA		—	—	0.4	V

* Vcc=5V, Ta=25°C

I/O Capacitance

(Ta=25°C, f=1MHz)

Item	Symbol	Test conditions	Min.	Max.	Unit
Input capacitance	C_{IN}	V_{IN}=0V	—	6	pF
I/O capacitance	$C_{I/O}$	$V_{I/O}$=0V	—	8	pF

Note) This parameter is sampled and is not 100% tested.

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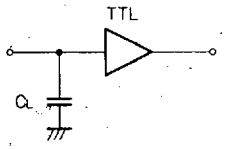
AC Characteristics

• AC test conditions

(Vcc=5V ± 10%, Ta=–25 to +85°C)

Item		Conditions
Input pulse high level		V_{IH}=2.4V
Input pulse low level		V_{IL}=0.6V
Input rise time		tr=5ns
Input fall time		tf=5ns
Input and output reference level		1.5V
Output load conditions	85LLX/10LLX/12LLX	C_L*=100pF, 1TTL
	70LLX	C_L*=30pF, 1TTL



* C_L includes scope and jig capacitances.

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• Read cycle

Item	Symbol	-70LLX		-85LLX		-10LLX		-12LLX		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read cycle time	t_{RC}	70	—	85	—	100	—	120	—	ns
Address access time	t_{AA}	—	70	—	85	—	100	—	120	ns
Chip enable access time	t_{CO}	—	70	—	85	—	100	—	120	ns
Output enable to output valid	t_{OE}	—	35	—	45	—	50	—	60	ns
Output hold from address change	t_{OH}	5	—	10	—	10	—	10	—	ns
Chip enable to output in low Z ($\overline{CE}$)	t_{LZ}	10	—	10	—	10	—	10	—	ns
Output enable to output in low Z ($\overline{OE}$)	t_{OLZ}	5	—	5	—	5	—	5	—	ns
Chip disable to output in high Z ($\overline{CE}$)	t_{HZ}*	0	30	0	30	0	30	0	30	ns
Chip disable to output in high Z ($\overline{OE}$)	t_{OHZ}*	0	30	0	30	0	30	0	30	ns

* t_{HZ} and t_{OHZ} are defined as the time required for outputs to turn to high impedance state and are not referred to as output voltage levels.

• Write cycle

Item	Symbol	-70LLX		-85LLX		-10LLX		-12LLX		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Write cycle time	t_{WC}	70	—	85	—	100	—	120	—	ns
Address valid to end of write	t_{AW}	65	—	75	—	80	—	100	—	ns
Chip enable to end of write	t_{CW}	65	—	75	—	80	—	100	—	ns
Data to write time overlap	t_{DW}	30	—	30	—	35	—	40	—	ns
Data hold from write time	t_{DH}	0	—	0	—	0	—	0	—	ns
Write pulse width	t_{WP}	50	—	50	—	60	—	70	—	ns
Address setup time	t_{AS}	0	—	0	—	0	—	0	—	ns
Write recovery time ($\overline{WE}$)	t_{WR}	5	—	5	—	5	—	5	—	ns
Write recovery time ($\overline{CE}$)	t_{WR1}	0	—	0	—	0	—	0	—	ns
Output active from end of write	t_{OW}	10	—	10	—	10	—	10	—	ns
Write to output in high Z	t_{WHZ}*	0	25	0	25	0	25	0	25	ns

* t_{WHZ} is defined as the time required for outputs to turn to high impedance state and is not referred to as output voltage level.

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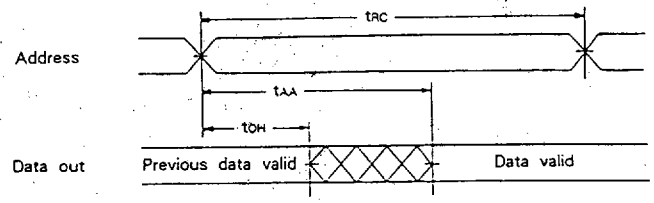
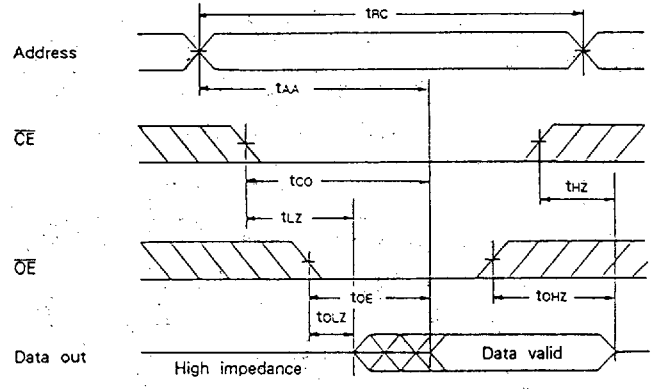
Timing Waveform

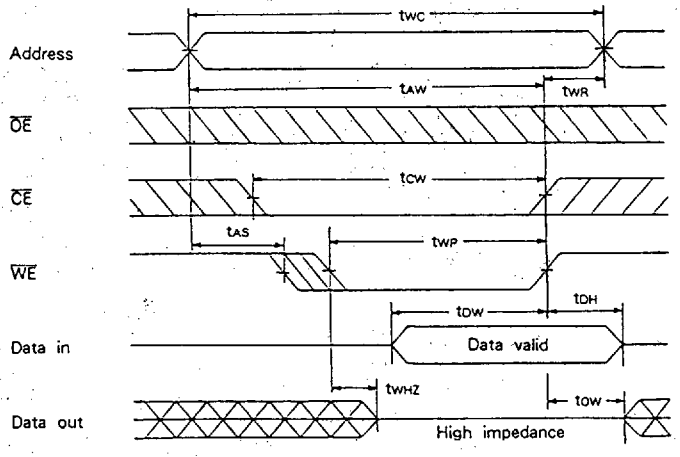
• Read cycle (1) : $\overline{CE}$=$\overline{OE}$=V_{IL}, $\overline{WE}$=V_{IH}



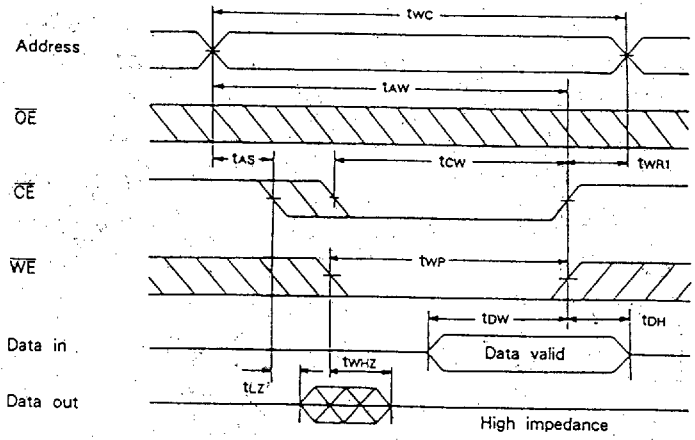
• Read cycle (2) : $\overline{WE}$=V_{IH}



• Write cycle (1) : $\overline{WE}$ control



• Write cycle (2) : $\overline{CE}$ control



During I/O pins are in the output state, the data input signals of opposite phase to the output must not be applied.

Data Retention Characteristics

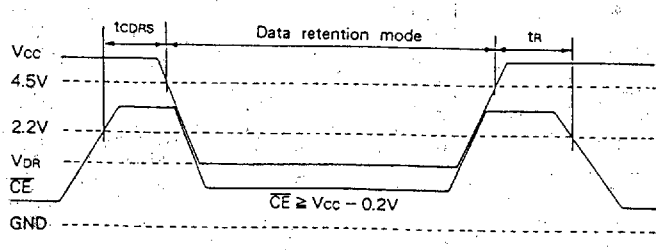
(Ta=−25 to +85°C)

Item	Symbol	Test conditions		−70LLX/85LLX/10LLX/12LLX Min.	Typ.	Max.	Unit
Data retention voltage	V_{DR}	$\overline{CE} \geqq V_{CC}-0.2V$		2.0	—	5.5	V
Data retention current	I_{CCDR1}	V_{CC}=3.0V $\overline{CE} \geqq$ 2.8V	−25 to +85°C	—	—	6	μA
			−25 to +70°C	—	—	3	
			−25 to +40°C	—	—	0.6	
			+25°C	—	0.1	0.3	
	I_{CCDR2}	V_{CC}=2.0 to 5.5V $\overline{CE} \geqq V_{CC}-0.2V$		—	0.2**	10	μA
Data retention setup time	t_{CDRS}	Chip disable to data retention mode		0	—	—	ns
Recovery time	t_R			t_{RC}*	—	—	ns

* t_{RC} : Read cycle time

** V_{CC}=5V, Ta=25°C

Data Retention Waveform



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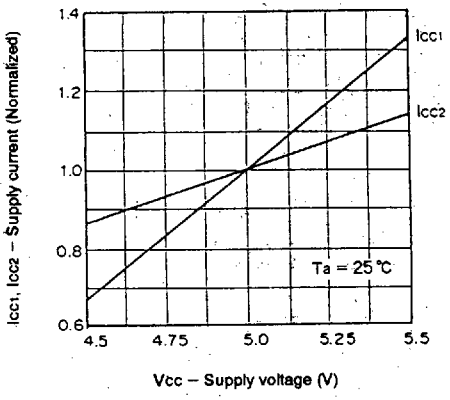
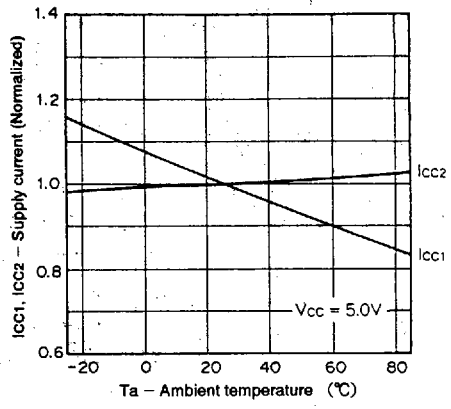
Example of Representative Characteristics

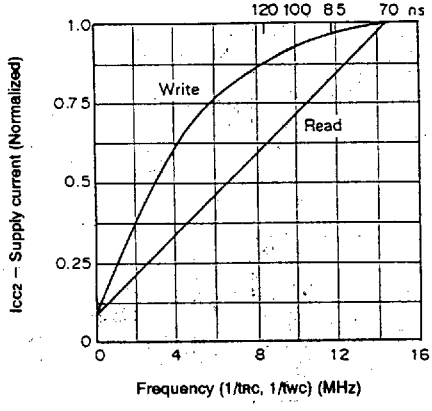
Supply current vs. Supply voltage



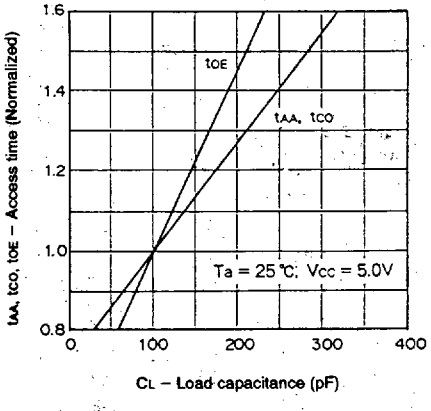
Supply current vs. Ambient temperature



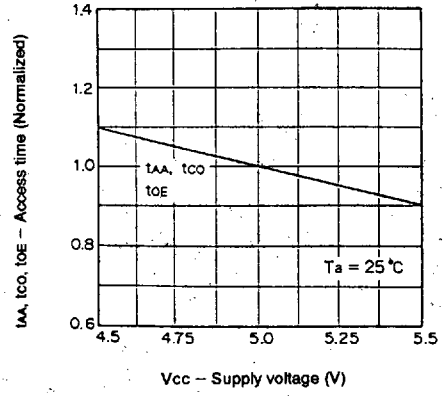
Supply current vs. Frequency



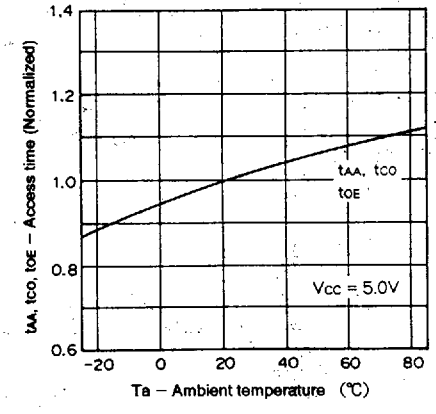
Access time vs. Load capacitance



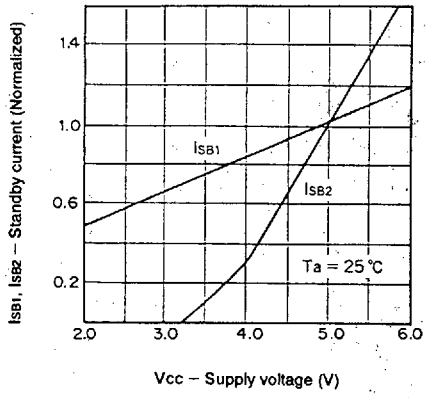
Access time vs. Supply voltage



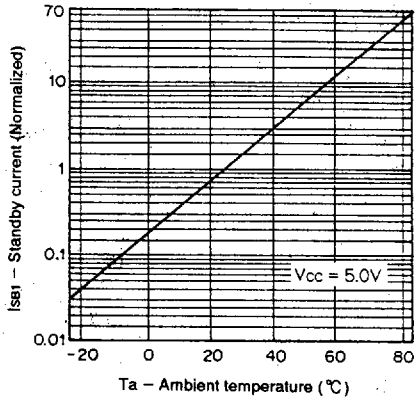
Access time vs. Ambient temperature



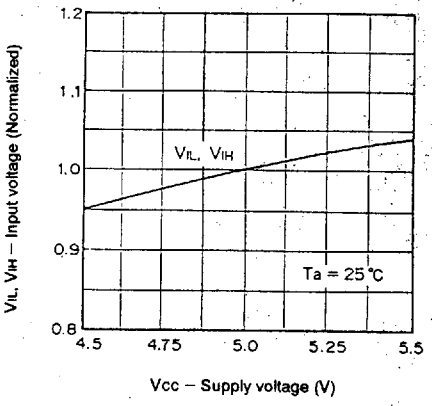
Standby current vs. Supply voltage



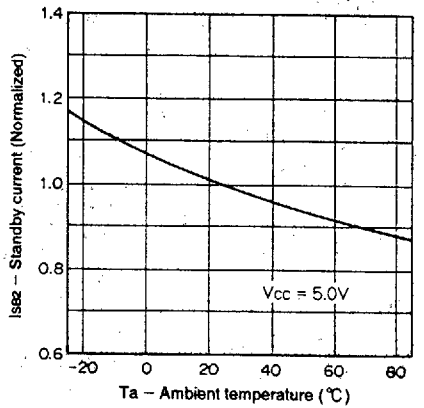
Standby current vs. Ambient temperature



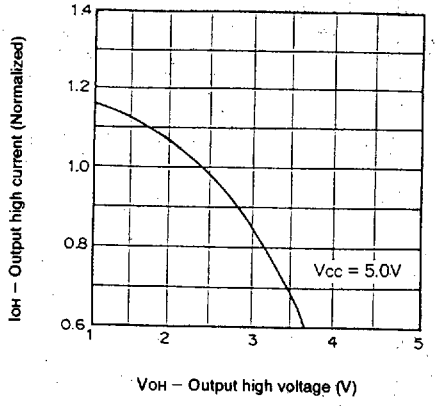
Input voltage level vs. Supply voltage



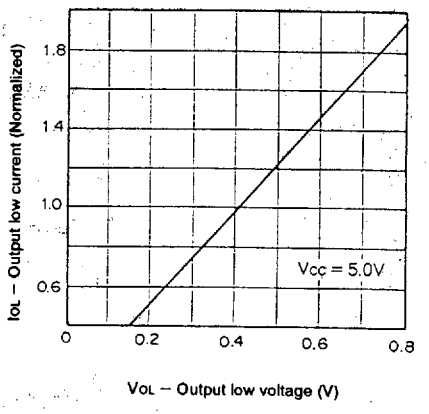
Standby current vs. Ambient temperature



Output high current vs. Output high voltage



Output low current vs. Output low voltage



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Package Outline

Unit : mm

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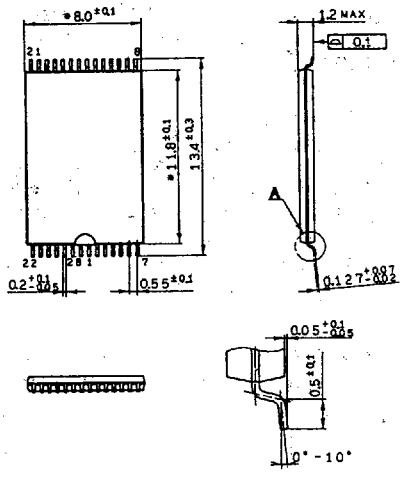
CXK58257ATM

28pin TSOP (Plastic)



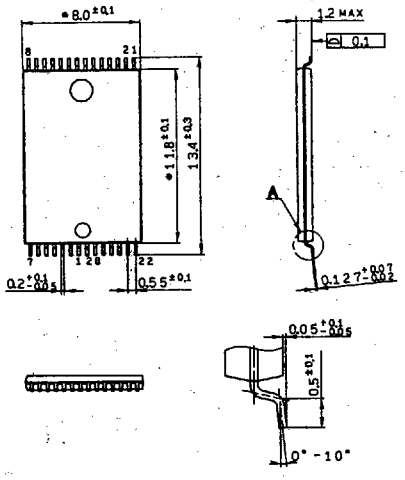
Detailed diagram of A

Note) Dimensions marked with * do not include resin residue.

SONY NAME	TSOP-28P-L01
EIAJ NAME	TSOP028-P-0000-A
JEDEC CODE	———

CXK58257AYM

28pin TSOP (Plastic)



Detailed diagram of A

Note) Dimensions marked with * do not include resin residue.

SONY NAME	TSOP-28P-L01R
EIAJ NAME	TSOP028-P-0000-B
JEDEC CODE	———